

**Amendments to the Specification:**

Please replace paragraph [0010] with the following amended paragraph:

[0010] The, the passivation layer **[25] 27** is patterned by **[the]** photolithography to define a contact hole 28 for exposing the drain electrode 23. A transparent conductive material such as indium tin oxide (ITO), tin oxide (TO) or indium zinc oxide (IZO) is deposited onto the passivation layer 27 in a manner to contact the drain electrode 23 via the contact hole 28. The transparent conductive material is then patterned by photolithography to form a pixel electrode 29.

Please replace paragraph [0016] with the following amended paragraph:

[0016] The invention, in part, pertains to the substrate having a temperature of less than about 200 °C, **[preferable] preferably** between about 50 °C and 150 °C, when forming the pixel substrate.